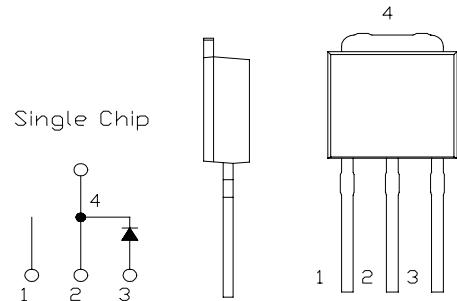


# SBD Type : EA30QS10

## OUTLINE DRAWING

### FEATURES

- \* TO-251AA Case
- \* Low Forward Voltage drop
- \* Low Power Loss
- \* High Surge Capability
- \* 40 Volts thru 100 Volts Types Available



### Maximum Ratings

Approx Net Weight:0.35g

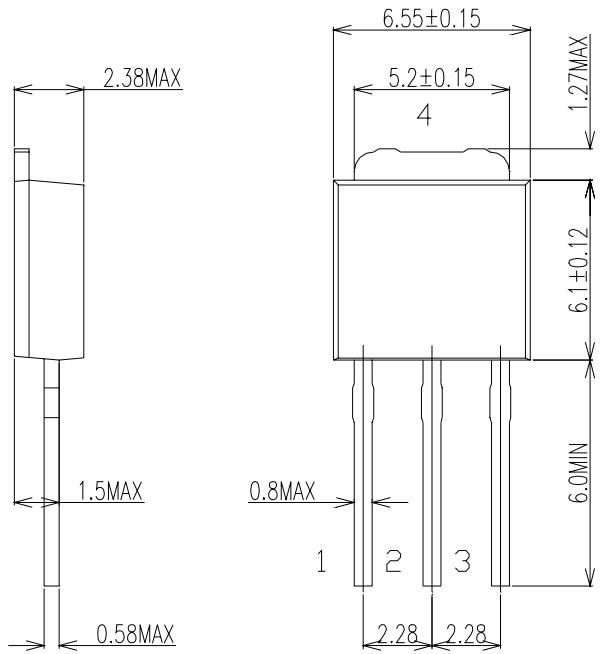
Rating	Symbol	EA30QS10				Unit	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	90				V	
Average Rectified Output Current	P.C.Board mounted *	Io	1.6	T <sub>a</sub> =34°C	50Hz Half Sine Wave Resistive Load	A	
		-	3.0	T <sub>c</sub> =133°C			
RMS Forward Current	I <sub>F(RMS)</sub>	4.71				A	
Surge Forward Current	I <sub>FSM</sub>	45	50Hz Half Sine Wave,1cycle, Non-repetitive				
Operating JunctionTemperature Range	T <sub>jw</sub>	- 40 to + 150				°C	
Storage Temperature Range	T <sub>stg</sub>	- 40 to + 150				°C	

### Electrical • Thermal Characteristics

Characteristics		Symbol	Conditions	Min	Typ	Max	Unit
Peak Reverse Current		I <sub>RM</sub>	T <sub>j</sub> =25°C, V <sub>RM</sub> =V <sub>RRM</sub>	-	-	1.0	mA
Peak Forward Voltage		V <sub>FM</sub>	T <sub>j</sub> =25°C, I <sub>FM</sub> = 3 A	-	-	0.85	V
Thermal Resistance	Junction to Ambient	R <sub>th(j-a)</sub>	P.C.Board mounted *	-	-	80	°C/W
	Junction to Case	R <sub>th(j-c)</sub>	-	-	-	6	°C/W

\* Print Land = 20x20 mm

**EA30QS10 OUTLINE DRAWING (Dimensions in mm)**



Single Chip

